METHOD FOR PRODUCING SEMICONDUCTOR SUBSTRATE

ABSTRACT OF THE DISCLOSURE

There is provided a method for suppressing the occurrence of defects such as voids or blisters even in the laminated wafer having no oxide film wherein hydrogen ions are implanted into a wafer for active layer having no oxide film on its surface to form a hydrogen ion implanted layer, and ions other than hydrogen are implanted up to a position that a depth from the surface side the hydrogen ion implantation is shallower than the hydrogen ion implanted layer, and the wafer for active layer is laminated onto a wafer for support substrate, and then the wafer for active layer is exfoliated at the hydrogen ion implanted layer.